

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 deg	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	Wafer Vendor
	5.0	Overall Thickness	675.00 +/- 18.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00 μ m	Guaranteed by Process
	7.0	Bow	<50.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<50.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	475.00 +/- 15.00 μ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1-100 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with no oxide & laser ID marking	Wafer Vendor
DeviceSilicon	18.0	Device Growth Method	CZ	Wafer Vendor
	19.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	20.0	Nominal Thickness	200.00 +/- 3.00 μ m	ADE Single Point, 100%
	21.0	Distance to device silicon edge from wafer edge	<= 3mm	Typical by Process
	22.0	Device Doping Type	P	Wafer Vendor
	23.0	Device Dopant	Boron	Wafer Vendor
	24.0	Device Resistivity	<0.001 Ohm-cm	Wafer Vendor
	25.0	Voids	0	Bright Light, 100% (note 2)
	26.0	Scratches	< 25mm total length	Bright Light, 100% (note 2)
	27.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information